

THE SPECIFICATION OF AlGaAs IR LED CHIP "IR3MH"

1. DESCRIPTION

This is a AlGaAs Infrared LED chip. It is P-side up. The peak wavelength is 850 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25°C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=16mA		1.8		V
Reverse Current (Ir) Vr=6V			10	uA
Radiated Power ¹⁾ (Po) IF=16mA		0.8		mW
Peak Wavelength (λ p) IF=16mA		850		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 30 mA(DC)
Reverse Voltage : 6 V(IR=10 μ A)

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1) Material : AlGaAs
2) Structure : Double Hetero Structure
3) Junction Size : 0.190mm × 0.330mm
4) Thickness : 0.280mm
5) Emission area : 0.080mm diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization: Gold Alloy

Physical Dimensions

Model IR3MH

UNIT:um

